NOTICE OF REVIS (See MIL-STD-480 fo This revision described below has been authorized fo	DATE (YYMMDD) 92-03-23	Form Approved OMB No. 0704-0188							
Public reporting burden for this collection is estimated to average 1 data needed, and completing and reviewing the collection of inform for reducing this burden, to Washington Headquarters Services, Di the Office of Information and Regulatory Affairs, Office of Managerr	hour per response, including the time for reviewing instru- action. Send comments regarding this burden estimate or rectorate for Information Operations and Reports, 1215 of tent and Budget, Washington, DC 20503.	ructions, searching existing data sources, or any other aspect of this collection of info lefferson Davis Highway, Suite 1204, Arli	, gathering and maintaining the ormation, including suggestions ngton, VA 22202-4302, and to						
1. ORIGINATOR NAME AND ADDRESS		2. CAGE CODE	3. NOR NO.						
Defense Electronics Supply Center		67268	5962-R164-92						
Dayton, Ohio 45444-5277		4. CAGE CODE	5. DOCUMENT NO.						
	67268	5962-88541							
6. TITLE OF DOCUMENT		7. REVISION LETTER							
MICROCIRCUITS, DIGITAL, 512 X 4-BIT B	POLAR PROM, MONOLITHIC	(Current) A	(New) B						
SILICON		8. ECP NO. No registered	users						
9. CONFIGURATION ITEM (OR SYSTEM) TO WH	ICH ECP APPLIES								
All									
All 10. DESCRIPTION OF REVISION Sheet 1: Revisions description column; add "Changes in accordance with NOR 5962-R164-92". Revisions date column; add "92-03-23". Sheet 2: Paragraph 1.2.2, to " <u>Outline letter</u> " add package "E", and to " <u>Case outline</u> " add D-2 (16-lead, .840" x .310" x .200") dual-in-line package. Sheet 4: Table I, Functional tests row. Device types column, delete "7,8" and add to Group A subgroups column. Sheet 7: Figure I, Terminal connections, delete "Case F" and substitute "Case E and F".									
11. THIS SECTION FOR GOVERNMENT USE ON	_Y								
a. CHECK ONE [X] EXISTING DOCUMENT SUPPLEMENTED [BY THIS NOR MAY BE USED IN MANUFACTURE.	REVISED DOCUMENT MUST BE RECEIVED BEFORE MANUFACTURER MAY INCORPORATE THIS CHANGE.	[] CUSTODIAN OF MASTEF SHALL MAKE ABOVE REV FURNISH REVISED DOC	R DOCUMENT VISION AND PUMENT TO:						
	SIGNATURE AND TITLE	DATE (YYMMDD)							
DESC-ECS	Michael Frye Branch Chief	92-03-23							
12. ACTIVITY ACCOMPLISHING REVISION	REVISION COMPLETED (Signature)	DATE (YYMMDD)							
DESC-ECS	Gary L. Gross	92-03-23							

								F	REVISI	ONS										
LTR	DESCRIPTION											DATE	(YR-MC)-DA)		APPROVED				
А	The 0 throug	1FX an ghout.	d 02FX	device	are ina	active fo	r new de	esigns.	Editori	ial chang	ges			91-0)4-19			Micha	el Frye	
REV																				
SHEET																				
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REV STATUS	6			REV	/		A	A	А		A	A					A			А
OF SHEETS				SHE	ET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A	NDAF	RD		PREP. MO	ARED NICA L	BY L. POEL	KING			DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444										
MICROCIRCUIT DRAWING THIS DRAWING IS AVAILABLE FOR USE BY ALL		CHEC RAY	KED B MONI	Y NIN																
			APPR MIC	OVED HAEL I	BY FRYE				MICF MON	MICROCIRCUIT, DIGITAL, 512 x 4-BIT BIPOLAR PRO MONOLITHIC SILICON			ROM,							
AND AGEN DEPARTMEN	ICIES IT OF	OF TI DEFE	HE INSE	DRAW 14 N	VING A //ARCH	\PPRO\ 1 1988	/AL DA ⁻	TE		SIZE		CAG	E COI	DE		50	62-	885	541	
AMS	5C N//	Ą		REVIS	ION LE	VEL	А			A			67268	5		55			/-+ 1	
										SH	EET	1		OF	14					

1. SCOPE								
1.1 <u>Scope</u> . "Provisions for th	This drawing de e use of MIL-ST	scribes device requirements fo D-883 in conjunction with com	or class B microcir pliant non-JAN dev	cuits in accordance with 1 <i>v</i> ices".	.2.1 of MIL-STD-883,			
1.2 Part or Ider	ntifying Number	(PIN). The complete PIN shall	be as shown in the	e following example:				
<u>59</u>	<u>62-88541</u>	01		<u>F</u>	<u>×</u>			
Dra	wing number	Device type (1.2.1)		Case outline (1.2.2)	Lead finish per MIL-M-38510			
1.2.1 <u>Device ty</u>	<u>/pe(s)</u> . The dev	ce type(s) shall identify the circu	uit function as follo	WS:				
Device type	Generic numbe	er <u>Circuit function</u>	<u>n A</u>	ccess time				
01 02	27S13A 27S13	512 x 4-bit bipolar PROM (thr 512 x 4-bit bipolar PROM (thr	ee-state) ee-state)	40 ns 60 ns				
1.2.2 Case out	<u>line(s)</u> . The cas	e outline(s) shall be as designat	ed in appendix C o	of MIL-M-38510, and as foll	ows:			
Outline lette	<u>r</u>	Case outline						
F 2		F-5 (16-lead, .440" x .285" x . C-2 (20-terminal, .358" x .358	085"), flat package " x .100"), square (e chip carrier package				
1.3 Absolute m	aximum ratings							
Supply voltage range $-0.5 V dc to +7.0 V dc$ Input voltage range $-0.5 V dc to +5.5 V dc$ Storage temperature range $-0.5 V dc to +5.5 V dc$ Maximum power dissipation (P _D) per device 1/ $-715 mW$ Lead temperature (soldering, 10 seconds) $+300^{\circ}C$ Thermal resistance, junction-to-case (Θ_{JC}) 2/See MIL-M-38510, appendix CJunction temperature (T _J) $175^{\circ}C$ DC voltage applied to outputs (except during programming) $-0.5 V dc to +5.5 V dc maximumDC voltage applied to outputs during-0.5 V dc to +5.5 V dc maximum$								
Output cu (maximul DC input c	rrent into output m duration of 1 current	s during programming s)	250 mA 30 mA to +5	5.0 mA				
1.4 <u>Recomme</u>	nded operating	conditions.						
Supply voltage range (V _{CC})								
<u>1</u> / Must withstan <u>2</u> / Heat sinking i	d the added P _D s recommended	due to short circuit test; e.g., I _C to reduce the junction tempera	oS [.] Iture.					
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2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standard, and bulletin</u>. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.

3.2.1 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.2 <u>Truth table</u>. The truth table shall be as specified on figure 2.

3.2.2.1 <u>Unprogrammed devices</u>. The truth table for unprogrammed devices shall be as specified on figure 2.

3.2.2.2 <u>Programmed devices</u>. The requirements for supplying programmed devices are not part of this drawing.

3.2.3 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.4 <u>Switching test circuit</u>. The switching test circuit shall be as specified on figure 4.

3.2.5 <u>Switching waveforms</u>. The switching waveforms shall be as specified on figure 5.

3.2.6 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.2 herein.

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		TABLE I. Electrical performa	nce characteris	stics.			
Test	Symbol	Conditions -55°C \leq T _C \leq +125°C	Group A Subgroups	Device types	Li	mits	Unit
		$4.5 \text{ V} \leq \text{V}_{CC} \leq 5.5 \text{ V}$ unless otherwise specified			Min	Max	
Output high voltage	V _{OH}	$V_{CC} = 4.5 \text{ V}, \text{ I}_{OH} = -2.0 \text{ mA}$ $V_{IH} = 2.0 \text{ V}, \text{ V}_{IL} = 0.8 \text{ V}$	1, 2, 3	All	2.4		V
Output low voltage	V _{OL}	$V_{CC} = 4.5 \text{ V}, I_{OL} = 16 \text{ mA}$ $V_{IH} = 2.0 \text{ V}, V_{IL} = 0.8 \text{ V}$	1, 2, 3			0.45	V
Input high level current	I _{IH}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 2.7 \text{ V}$	1, 2, 3			25	uA
Input low level current	I _{IL}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 0.45 \text{ V}$	1, 2, 3			-250	uA
Power supply current	Icc	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 0.0 \text{ V}$	1, 2, 3			130	mA
Input clamp voltage	VI	V _{CC} = 4.5 V, V _{IN} = -18 mA	1, 2, 3			-1.2	V
High output leakage current	I _{OZH}	$V_{CC} = 5.5 V$ $V_{O} = 4.5 V$ $V_{CS} = 2.4 V$	1, 2, 3			40	uA
	I _{OZL}	$V_{IH} = 2.0 V$ $IL_C = 0.8 V$ $V_O = 0.4 V$				-40	
Output short circuit current	I _{OS}	V _{CC} = 5.5 V V _{OUT} = 0.0 V <u>1</u> /	1, 2, 3		-20	-90	mA
Functional tests		See 4.3.1d		7, 8			
Address access time	t _{AVQV}	$C_L = 50 pF$	9, 10, 11	01		40	ns
		(See figures 4 and 5)		02		60	
Enable access time	t _{GVQV}	(See figures 4 and 5) <u>2</u> /	9, 10, 11	01		25	ns
				02		30	
Enable recovery time	t _{GVQZ}	(See figures 4 and 5) <u>2</u> /	9, 10, 11	01		25	ns
				02		30	

1/ Not more than one output should be shorted at a time and the duration of the short circuit condition should not exceed one second.

 $2/t_{GVQV}$ is tested with C_L = 50 pF to the 1.5 V level; S1 is open for high impedance to high tests and closed for high impedance to low tests. t_{GVQZ} is tested with C_L = 5 pF. High to high impedance tests are made with S1 open to an output voltage of V_{OH} -0.5 V. Low to high impedance tests are made with S1 closed to the V_{OL} +0.5 V level.

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3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and apply over the full case operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

3.5 <u>Marking</u>. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103 (see 6.6 herein).

3.6 <u>Processing options</u>. Since the PROM is an unprogrammed memory capable of being programmed by either the manufacturer or the user to result in a wide variety of PROM configurations, two processing options are provided for selection in the contract, using an altered item drawing.

3.6.1 <u>Unprogrammed PROM delivered to the user</u>. All testing shall be verified through group A testing as defined in 4.3.1. It is recommended that users perform subgroups 7 and 9 after programming to verify the specific program configuration.

3.6.2 <u>Manufacturer-programmed PROM delivered to the user</u>. All testing requirements and quality assurance provisions herein, including the requirements of the altered item drawing shall be satisfied by the manufacturer prior to delivery.

3.7 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.6 herein). The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.

3.8 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.

3.9 <u>Notification of change</u>. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).

3.10 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

4. QUALITY ASSURANCE PROVISIONS

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).

4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition C or D using the circuit submitted with the certificate of compliance (see 3.7 herein).

- (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.

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4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

4.3.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Unprogrammed devices shall be tested for programmability and ac performance compliance to the requirements of group A, subgroups 9, 10, and 11. Either of two techniques is acceptable.
 - (1) Testing the entire lot using additional built-in test circuitry which allows the manufacturer to verify programmability and performance without programming the user array. If this is done, the resulting test pattern shall be verified on all devices during subgroups 9, 10, and 11, group A testing in accordance with the sampling plan specified in MIL-STD-883, method 5005.
 - (2) If such compliance cannot be tested on an unprogrammed device, a sample shall be selected to satisfy programmability requirements prior to performing subgroups 9, 10, and 11. Twelve devices shall be submitted to programming (see 3.2.2.2). If more than two devices fail to program, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 24 total devices with no more than four total device failures allowed. Ten devices from the programmability sample shall be submitted to the requirements of group A, subgroups 9, 10, and 11. If more than two total devices fail, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 20 total devices with no more than four total device failures allowable.
- d. Subgroups 7 and 8 shall include verification of the truth table.

4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition C or D using the circuit submitted with the certificate of compliance (see 3.7 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- c. The group C, subgroup 1 sample shall include devices tested in accordance with 4.3.1.c.

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per mehtod 5005, table I)		
Interim electrical parameters (method 5004)			
Final electrical test parameters (method 5004)	1*, 2, 3, 7*, 8, 9, 10**, 11**		
Group A test requirements (method 5005)	1, 2, 3, 7, 8, 9, 10**, 11**		
Group C and D end-point electrical parameters (method 5005)	1, 2, 3		

* PDA applies to subgroups 1 and 7.

** Subgroups 10 and 11, if not tested, shall be guaranteed to the limits specified in table I.

4.4 Programming procedures for method A.

- a. Connect the device in the electrical configuration for programming. The waveforms on figure 6 and the programming characteristics of table III shall apply to these procedures.
- b. Terminate all outputs to V_{ONP} through a pull-up resistor R.
- c. Apply V_{CCP} to V_{CC}.
- d. Connect \overline{CS} to V_{ILP} .
- e. Address the PROM with the binary address of the selected word to be programmed.
- f. After a delay of t₁, apply V_{OP} for a duration of t_P + rise time of CS input + t₂ to the output selected for programming. After a delay of t₂ + rise time of programmed output, apply V_{CSP} for a duration of t_P + rise time of programmed output + t₃ to the CS input; CS is then reduced to V_{II P}.
- g. After a delay of t₄, opening of the fuse is verified. During verification, V_{CC} remains unchanged at V_{CCP}.
- h. The outputs should be programmed one at a time, since the internal decoding circuitry is capable of sinking only one unit of programming current at a time. Note that the PROM is supplied with fuses generating a low level logic output. Programming a fuse will cause the output to go to a high level logic in the verify mode.
- i. Repeat steps 4.4a through 4.4g for all bits to be programmed.
- j. If any unit does not verify as programmed, it shall be considered a programming reject.

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Test	Symbol	Conditions	Li	mits	Unit
		l _C = +25°C 4.5 V ≤ V _{CC} ≤ 5.5 V	Min	Max	
V _{CC} during programming	V _{CCP}		5.0	5.5	V
High level input voltage during programming	V _{IHP}		2.4	5.5	V
Low level input voltage during programming	V _{ILP}		0.0	0.45	V
Chip select voltage during programming	V _{CSP}		14.5	15.5	V
Output voltage during programming	V _{OP}		19.5	20.5	V
Voltage on outputs not to be programmed	V _{ONP}		0	V _{CCP} +0.3	V
Current into outputs not to be programmed	I _{ONP}			20	mA
Rate of output voltage change	d(V _{OP}) dt		20	250	V/uS
Rate of chip select voltage change	$\frac{d(V_{CS})}{dt}$		100	1000	V/uS
Programming period	t _P		50	100	uS

TABLE III. Programming characteristics for method A.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-M-38510.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.

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- 6.2 <u>Replaceability</u>. Replaceability is determined as follows:
 - a. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - b. When a QPL source is established, the device specified in this drawing will be replaced by the microcircuit identified as PIN M38510/204B--.

6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).

6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6022.

6.5 <u>Comments</u>. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5375.

6.6 <u>Approved sources of supply</u>. Approved sources of supply are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-ECS.

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STANDARD MICROCIRCUIT DRAWING SOURCE APPROVAL BULLETIN

DATE: 91-04-19

Approved sources of supply for SMD 5962-88726 are listed below for immediate acquisition only and shall be added to MIL-BUL-103 during the next revision. MIL-BUL-103 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DESC-ECS. This bulletin is superseded by the next dated revision of MIL-BUL-103.

Standardized military drawing PIN	Vendor CAGE number	Vendor similar part number <u>1</u> /	Replacement military specification PIN
5962-8854101FX	<u>2</u> /	S13A AM27/BFA	M38510/20404BFX
5962-88541012X	34335	AM27S13A/B2A	
5962-8854102FX	<u>2</u> /	AM27S13/BFA	M38510/20404BFX
5962-88541022X	34335	AM27S13/B2A	

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

2/ Inactive for new design, use M38510/20404BFX

Vendor CAGE	Vendor name	Programming	Fusible
number	<u>and address</u>	<u>procedure</u>	<u>link</u>
34335	Advanced Micro Devices, Incorporated 901 Thompson Place P.O. Box 3453 Sunnyvale, CA 94088	A	Platinum silicide fuse

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in this information bulletin.